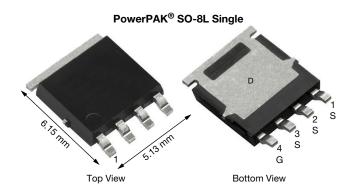


www.vishay.com

Vishay Siliconix

# Automotive P-Channel 12 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY					
V <sub>DS</sub> (V)	-12				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.0058				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -2.5 \text{ V}$	0.0087				
I <sub>D</sub> (A)	-60				
Configuration	Single				
Package	PowerPAK SO-8L				

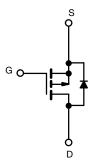
#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % Rq and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



P-Channel MOSFET

ABSOLUTE MAXIMUM RATING	<b>S</b> (T <sub>C</sub> = 25 °C, unles	s otherwise noted	)		
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	$V_{DS}$	-12			
Gate-Source Voltage	V <sub>GS</sub>	± 8	V		
Continuous Drain Current	T <sub>C</sub> = 25 °C <sup>a</sup>	I-	-60		
	T <sub>C</sub> = 125 °C	- I <sub>D</sub>	-52		
Continuous Source Current (Diode Conduction	Is	-60	Α		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	-110		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	-30		
Single Pulse Avalanche Energy	L = 0.1 IIIH	E <sub>AS</sub>	45	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	В	68	W	
	T <sub>C</sub> = 125 °C	$P_{D}$	22	VV	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
Soldering Recommendations (Peak Temperature) d, e			260	l	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount c	$R_{thJA}$	68	°C/W
Junction-to-Case (Drain)		$R_{thJC}$	2.2	C/VV

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. See Solder Profile (<a href="https://www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The PowerPAK SO-8L. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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<b>SPECIFICATIONS</b> ( $T_C = 25  ^{\circ}C$ , t		/ise noted)			_		
PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	$V_{DS}$	V <sub>GS</sub>	= 0, I <sub>D</sub> = -250 μA	-12		-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =	$V_{GS}$ , $I_D = -250 \mu A$	-0.45	-0.6	-1.5	V
Gate-Source Leakage	$I_{GSS}$	V <sub>DS</sub> =	$= 0 \text{ V}, \text{ V}_{GS} = \pm 8 \text{ V}$	ı	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = -12 V	1	-	-1	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0 V$	V <sub>DS</sub> = -12 V, T <sub>J</sub> = 125 °C	1	-	-50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -12 V, T <sub>J</sub> = 175 °C	-	-	-250	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = -4.5 V	V <sub>DS</sub> ≤ -5 V	-30	-	-	Α
		V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -15 A	-	0.0048	0.0058	
Drain Course On State Desigtance 2	В	V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -15 A, T <sub>J</sub> = 125 °C	-	-	0.0074	
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -15 A, T <sub>J</sub> = 175 °C	-	-	0.0082	Ω
		V <sub>GS</sub> = -2.5 V	I <sub>D</sub> = -10 A	-	0.0072	0.0087	
Forward Transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> =	-15 V, I <sub>D</sub> = -15 A	-	73	-	S
Dynamic <sup>b</sup>		•					ı
Input Capacitance	C <sub>iss</sub>			-	6990	9100	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = -6 V, f = 1 MHz	1	2450	3200	pF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	1960	2600	
Total Gate Charge <sup>c</sup>	Qg			1	99	150	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = -4.5 V	$V_{DS} = -6 \text{ V}, I_{D} = -1 \text{ A}$	1	12	-	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	29	-	
Gate Resistance	$R_g$		f = 1 MHz	0.5	1.1	1.7	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	32	50	
Rise Time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub>	= -6 V, $R_1 = 6 \Omega$	-	36	60	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	I <sub>D</sub> ≅ -1 A, \	$I_{\rm GEN} = -4.5 \text{ V}, R_{\rm g} = 1 \Omega$	=	198	300	ns
Fall Time <sup>c</sup>	t <sub>f</sub>			1	75	115	
Source-Drain Diode Ratings and Charac	cteristics <sup>b</sup>						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	-110	Α
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> =	-15 A, V <sub>GS</sub> = 0	-	-0.8	-1.2	V
Body diode reverse recovery time	t <sub>rr</sub>			-	79	160	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	] , , <u>,</u>	A 11/11 400 A/	-	119	240	nC
Reverse recovery fall time	ta	I <sub>F</sub> = -10	A, di/dt = 100 A/μs	-	37	-	
Reverse recovery rise time	t <sub>b</sub>	1		-	47	-	ns
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>			-	-2.7	-6	Α

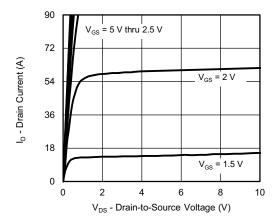
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

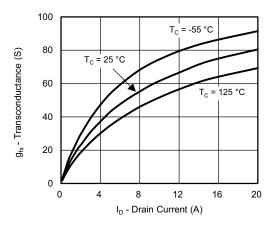
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



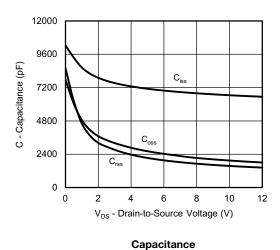
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



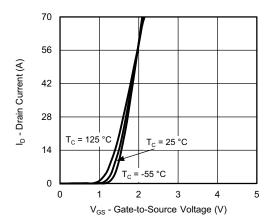
#### **Output Characteristics**



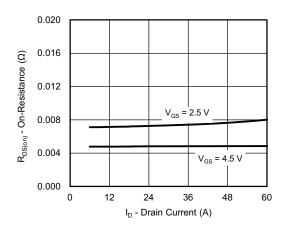
Transconductance



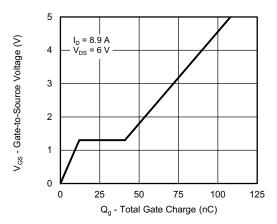
ACTEMICATION (TA = 20 °C, arricos otrior wise riotes



**Transfer Characteristics** 



On-Resistance vs. Drain Current

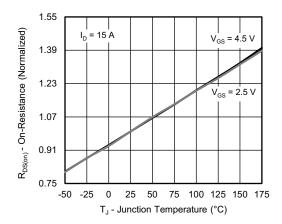


**Gate Charge** 

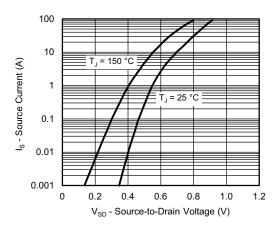
For technical questions, contact: automostechsu



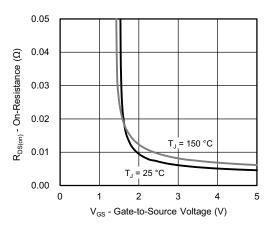
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



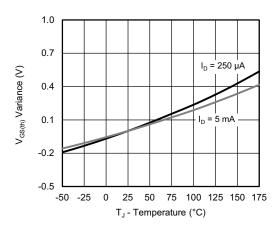
On-Resistance vs. Junction Temperature



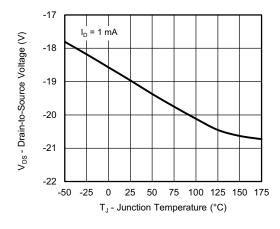
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



**Threshold Voltage** 

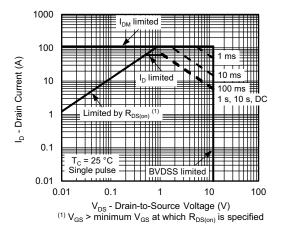


**Drain Source Breakdown vs. Junction Temperature** 

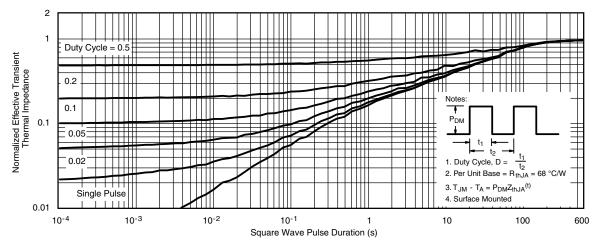
For technical questions, contact: automostech



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



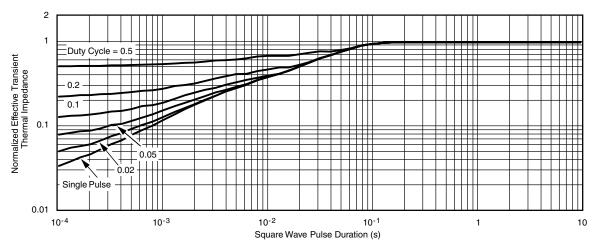
#### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

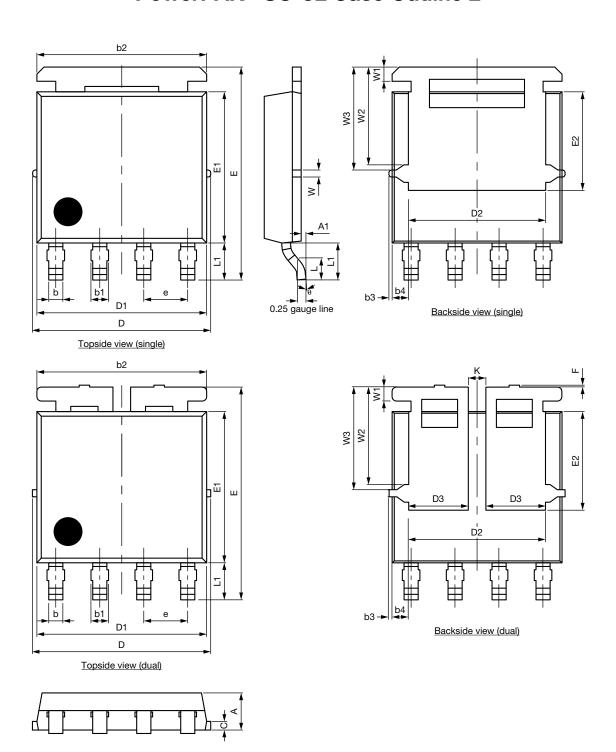
#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg276549">www.vishay.com/ppg276549</a>.



# PowerPAK® SO-8L Case Outline 2



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DIM		MILLIMETERS		INCHES		
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
А	1.00	1.07	1.14	0.039	0.042	0.045
A1	0.00	-	0.127	0.00	-	0.005
b	0.33	0.41	0.48	0.013	0.016	0.019
b1	0.44	0.51	0.58	0.017	0.020	0.023
b2	4.80	4.90	5.00	0.189	0.193	0.197
b3		0.094		0.004		
b4		0.47			0.019	
С	0.20	0.25	0.30	0.008	0.010	0.012
D	5.00	5.13	5.25	0.197	0.202	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.86	3.96	4.06	0.152	0.156	0.160
D3	1.63	1.73	1.83	0.064	0.068	0.072
е		1.27 BSC			0.050 BSC	
Е	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	2.75	2.85	2.95	0.108	0.112	0.116
F	-	-	0.15	-	-	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K		0.51			0.020	
W	0.23		0.009			
W1	0.41		0.016			
W2	2.82			0.111		
W3	2.96			0.117		
θ	0°	-	10°	0°	-	10°

ECN: C21-1498-Rev. C, 01-Nov-2021

DWG: 6044

#### Note

• Millimeters will govern



#### RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



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